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Microwave properties of $YBa_2Cu_3O_{7-\delta}$ films with $BaZrO_3$ nanoinclusions.

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Abstract

We present measurements of the microwave complex surface impedance at 47.7 GHz in $YBa_2Cu_3O_{7-\delta}$ (YBCO) films deposited by pulsed laser deposition with the explicit goal to introduce $BaZrO_3$ (BZO) nanoinclusions. Composite targets obtained by addition of BZO powder in molar percents ranging from 2.5 to 7 mol.% have been prepared and characterized. Measurements of the microwave surface impedance indicate a broadened transition in zero field, however compensated by a very large pinning frequency, indicating that while intergrain properties are still to be optimized the effect of nanometric inclusions substantially enhances the intragrain vortex pinning.

Key words: $YBa_2Cu_3O_{7-\delta}$, $BaZrO_3$ inclusions, pinning frequency, surface impedance
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Various techniques have been exploited in order to improve vortex pinning and reduce vortex motion. In films both intergrain (grain boundary dominated, GB) and intragrain phenomena play a role in determining the magnetic field-dependent dissipation properties. While GB dissipation dominates at low magnetic fields, the intra-grain mechanisms constitute the ultimate limitation. Film texture is beneficial for reducing GB dissipation, while the introduction of artificial defects of order of the vortex diameter ($\sim$ the coherence length) can be effective in order to increase vortex pinning and reduce vortex motion. In the attempt of achieving high-J_c YBCO coated conductor a renewed interest arose about the investigation of novel or improved techniques for the introduction of pinning centers. A possible, feasible method to introduce such defects is the inclusion of nanometer-size particles in the target used for film deposition [1]. We have grown YBCO films (thicknes d $\sim$200 nm) with BZO inclusions by pulsed laser ablation [2] starting from mixed YBCO-BZO sintered targets with various BZO concentration ranging from 7 to 2.5 percent, on single crystal $SrTiO_3$ and CeO_2 buffered r-cut alpha Al_2O_3 (for microwave measurements) substrates. The dc zero resistance critical temperature T_c revealed a slight dependence on the BZO content (inset of Fig.1). We focus here on the results

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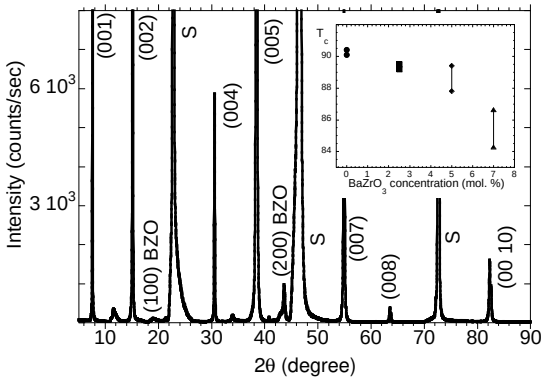


Fig. 1. X-ray $\theta - 2\theta$ scan. Inset: T_c vs. BZO content.

obtained on the 7% samples. Only (00l) YBCO and substrate (S) peaks are visible in the $\theta - 2\theta$ scan (Fig. 1), indicating a good epitaxy. ω scan through the (005) YBCO peak exhibits FWHM of 0.1°. Other reflections at about 21.5° and 43.7° are present, ascribable to (h00) BZO.

The measurement of the microwave response in the vortex state is a particularly stringent test of the pinning properties, since small vortex oscillations are involved and one tests both the presence of pinning centers and the steepness of the potential well. Not too close to T_c, and when the field dependence of the complex resistivity is linear, the simplest models for fluxon motion [3] can be applied, and one has:

$$\frac{\Delta\rho_1 + \mathrm{i}\Delta\rho_2}{\Delta B} = \frac{\Phi_0}{\eta} \frac{1 + \mathrm{i}\frac{\nu_p}{\nu}}{1 + \left(\frac{\nu_p}{\nu}\right)^2} \qquad (1)$$

where $\Delta\rho$ is the complex resistivity change due to a field variation ΔB, η is the fluxon viscosity and the pinning frequency ν_p (∼10 GHz above 70 K in YBCO crystals [4]) is a measure of the steepness of the potential well for the flux lines.

We measured the microwave response at 47.7 GHz by means of a dielectric resonator operating in the TE_{011} mode. The temperature and field dependence of Q factor and resonant frequency yielded the complex resistivity $\rho_1 + \mathrm{i}\Delta\rho_2$. In Fig.2 we report ρ_1 and $\rho_2(T,H) - \rho_2(T,0)$ at some selected field. It is seen that the transition is rather broad, as somehow expected: microwaves probe the whole thickness of the film, and an area of order ∼5 mm^2, so that the effect of nonsuperconducting inclusions

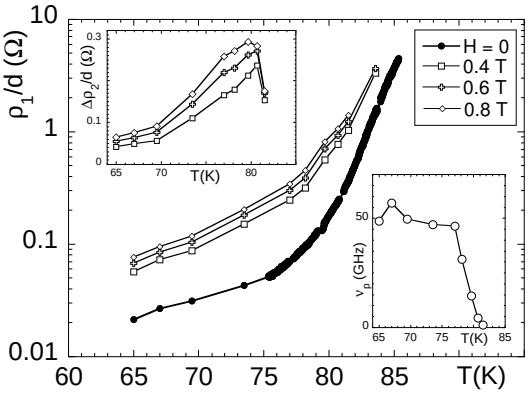


Fig. 2. Microwave complex resistivity at 47.7 GHz at different fields. Main panel: ρ_1/d. Upper inset: $\Delta\rho_2/d = [\rho_2(H,T) - \rho_2(0,T)]/d$. Lower inset: estimate of ν_p using Eq.1.

and of the disorder introduced shows up as a broadening of the transition. In the vortex state many processes are in general responsible for the microwave response. We found that a large part of the dissipation was sublinear at low fields, probably indicating GB phenomena. At fields larger than ∼ 0.4 T the complex response was linear in the applied field. We report in the inset of Fig.2 ν_p as determined from the data using Eq.1. Very high values ν_p ∼50 Ghz are attained up to 77 K, indicating extremely high vortex pinning and steep potential wells. As expected, the pinning frequency rapidly drops to zero as $T \to T_c$. We conclude that the introduction of BZO inclusion of nanometric size in YBCO films has improved the intragrain vortex pinning at high microwave frequencies. While the effect of the inclusions on GB needs further study, it appears promising for improving intragrain pinning.

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